

Quad SPST CMOS Analog Switches

DESCRIPTION

The DG441, DG442 monolithic quad analog switches are designed to provide high speed, low error switching of analog and audio signals. The DG441 has a normally closed function. The DG442 has a normally open function. Combining low on-resistance (50 Ω , typ.) with high speed (t_{on} 150 ns, typ.), the DG441, DG442 are ideally suited for upgrading DG201A/202 sockets. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

To achieve high voltage ratings and superior switching performance, the DG441, DG442 are built on Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages to the supply levels when off.

BENEFITS

- Less signal errors and distortion
- Reduced power supply requirements
- Faster throughput
- Improved reliability
- Reduced pedestal errors
- Simplifies retrofit
- Simple interfacing

FEATURES

- Low on-resistance: 50 Ω
- Low leakage: 80 pA
- Low power consumption: 0.2 mW
- Fast switching action - t_{on} : 150 ns
- Low charge injection - Q: - 1 pC
- DG201A/DG202 upgrades
- TTL/CMOS-compatible logic
- Single supply capability
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

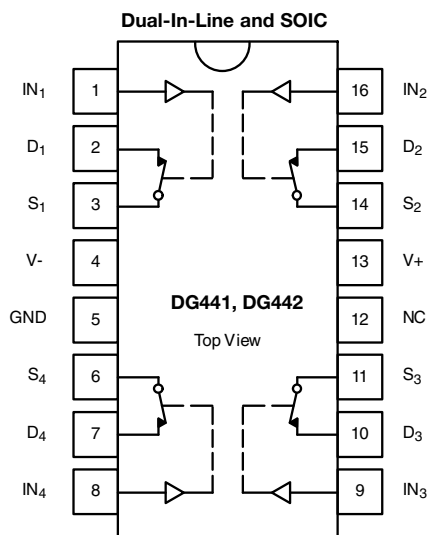


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Audio switching
- Battery powered systems
- Data acquisition
- Hi-Rel systems
- Sample-and-hold circuits
- Communication systems
- Automatic test equipment
- Medical instruments

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE

LOGIC	DG441	DG442
0	On	Off
1	Off	On

Note

- Logic "0" ≤ 0.8 V
- Logic "1" ≥ 2.4 V

**ORDERING INFORMATION**

TEMP. RANGE	PACKAGE	PART NUMBER
-40 °C to +85 °C	16-pin narrow SOIC	DG441DY-E3 DG441DY-T1-E3
		DG442DY-E3 DG442DY-T1-E3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$, unless otherwise noted)

PARAMETER		LIMIT	UNIT
Voltages referenced, V+ to V-		44	V
GND to V-		25	
Digital inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first	
Current (any terminal)		30	mA
Peak current, S or D (pulsed at 1 ms, 10 % duty cycle max.)		100	
Storage temperature	(AK suffix)	-65 to +150	°C
	(DJ, DY suffix)	-65 to +125	°C
Power dissipation (package) ^b	16-pin narrow SOIC ^d	600	mW

Notes

- a. Signals on SX, DX, or INX exceeding V_+ or V_- will be clamped by internal diodes. Limit forward diode current to maximum current ratings
b. All leads welded or soldered to PC board
c. Derate 6 mW/°C above 75 °C
d. Derate 7.6 mW/°C above 75 °C

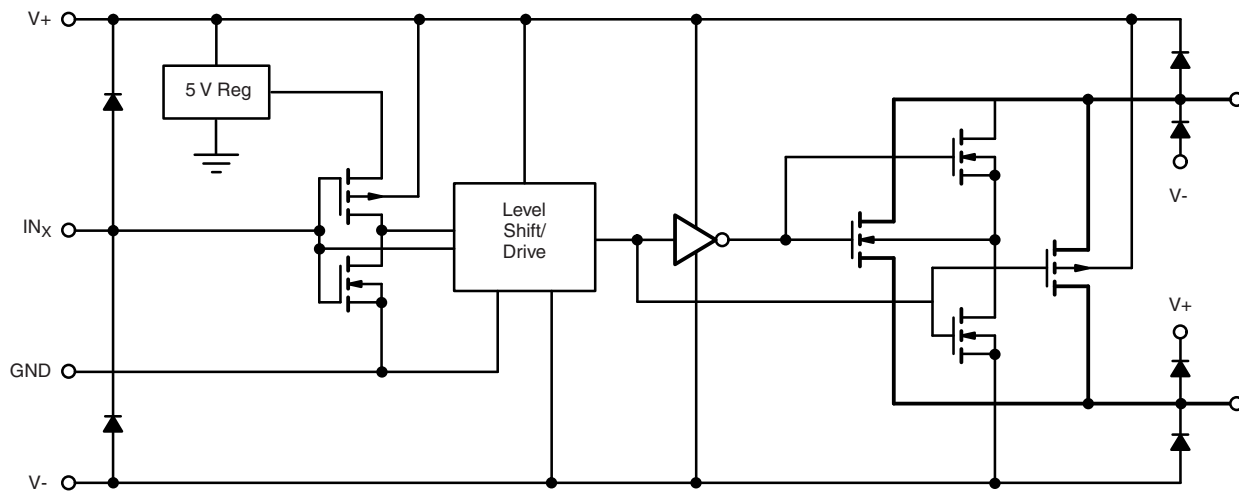
SCHEMATIC DIAGRAM (typical channel)

Fig. 1

SPECIFICATIONS ^a (dual supplies)

PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 15 V, V- = -15 V VIN = 2.4 V, 0.8 V ^f	TEMP. ^b	TYP. ^c	A SUFFIX -55 °C TO +125 °C		D SUFFIX - 40 °C TO +85 °C		UNIT
					MIN. ^d	MAX. ^d	MIN. ^d	MAX. ^d	
Analog Switch									
Analog signal range ^e	V _{ANALOG}		Full	-	-15	15	-15	15	V



SPECIFICATIONS ^a (dual supplies)										
PARAMETER		SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 15 V, V ₋ = -15 V V _{IN} = 2.4 V, 0.8 V ^f	TEMP. ^b	TYP. ^c	A SUFFIX -55 °C TO +125 °C		D SUFFIX - 40 °C TO +85 °C		UNIT
						MIN. ^d	MAX. ^d	MIN. ^d	MAX. ^d	
Drain-source on-resistance		R _{DS(on)}	I _S = -10 mA, V _D = ± 8.5 V, V ₊ = 13.5 V, V ₋ = -13.5 V	Room	50	-	85	-	85	Ω
				Full	-	-	100	-	100	
On-resistance match between channels ^e		ΔR _{DS(on)}	I _S = -10 mA, V _D = ± 10 V, V ₊ = 15 V, V ₋ = -15 V	Room	-	-	4	-	4	
				Full	-	-	5	-	5	
Switch off leakage current		I _{S(off)}	V ₊ = 16.5, V ₋ = -16.5 V, V _D = ± 15.5 V, V _S = ± 15.5 V	Room	± 0.01	-0.5	0.5	-0.5	0.5	nA
				Full	-	-20	20	-5	5	
		I _{D(off)}		Room	± 0.01	-0.5	0.5	-0.5	0.5	
				Full	-	-20	20	-5	5	
Channel on leakage current		I _{D(on)}	V ₊ = 16.5 V, V ₋ = -16.5 V, V _S = V _D = ± 15.5 V	Room	± 0.08	-0.5	0.5	-0.5	0.5	
				Full	-	-40	40	-10	10	
Digital Control										
Input current V _{IN} low		I _{IL}	V _{IN} under test = 0.8 V, all other = 2.4 V	Full	-0.01	-500	500	-500	500	nA
Input current V _{IN} high		I _{IH}	V _{IN} under test = 2.4 V, all other = 0.8 V	Full	0.01	-500	500	-500	500	
Dynamic Characteristics										
Turn-on time		t _{on}	R _L = 1 kW, C _L = 35 pF, V _S = ± 10 V, see Fig. 2	Room	150	-	250	-	250	ns
Turn-off time	DG441	t _{off}		Room	90	-	120	-	120	
	DG442			Room	110	-	210	-	210	
Charge injection ^e		Q	C _L = 1 nF, V _S = 0 V, V _{gen} = 0 V, R _{gen} = 0 Ω	Room	-1	-	-	-	-	pC
Off Isolation ^e		OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room	60	-	-	-	-	dB
Crosstalk (channel-to-channel)		X _{TALK}		Room	100	-	-	-	-	
Source off capacitance ^e		C _{S(off)}	f = 1 MHz	Room	4	-	-	-	-	pF
Drain off capacitance ^e		C _{D(off)}		Room	4	-	-	-	-	
Channel on capacitance ^e		C _{D(on)}		Room	16	-	-	-	-	
Power Supplies										
Positive supply current		I ₊	V ₊ = 16.5 V, V ₋ = -16.5 V, V _{IN} = 0 V or 5 V	Full	15	-	100	-	100	μA
Negative supply current		I ₋		Room	-0.0001	-1	-	-1	-	
				Full	-	-5	-	5	-	
				Full	-15	-100	-	-100	-	
Ground current		I _{GND}								



SPECIFICATIONS ^a (single supply)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 12 V, V ₋ = 0 V, V _{IN} = 2.4 V, 0.8 V ^f	TEMP. ^b	TYP. ^c	A SUFFIX -55 °C TO +125 °C		D SUFFIX - 40 °C TO +85 °C		UNIT
					MIN. ^d	MAX. ^d	MIN. ^d	MAX. ^d	
Analog Switch									
Analog signal range ^e	V _{ANALOG}		Full	-	0	12	0	12	V
Drain-source on-resistance	R _{DS(on)}	I _S = -10 mA, V _D = 3 V, 8 V, V ₊ = 10.8 V	Room	100	-	160	-	160	Ω
			Full	-	-	200	-	200	
Dynamic Characteristics									
Turn-on time	t _{on}	R _L = 1 kΩ, C _L = 35 pF V _S = 8 V, see Fig. 2	Room	300	-	450	-	450	ns
Turn-off time	t _{off}		Room	60	-	200	-	200	
Charge injection	Q	C _L = 1nF, V _{gen} = 6 V, R _{gen} = 0 Ω	Room	2	-	-	-	-	pC
Power Supplies									
Positive supply current	I ₊	V ₊ = 13.2 V, V ₋ = 0 V, V _{IN} = 0 or 5 V	Full	15	-	100	-	100	μA
Negative supply current	I ₋		Room	-0.0001	-1	-	-1	-	
			Full	-	-100	-	-100	-	
Ground current	I _{GND}		Full	-15	-100	-	-100	-	

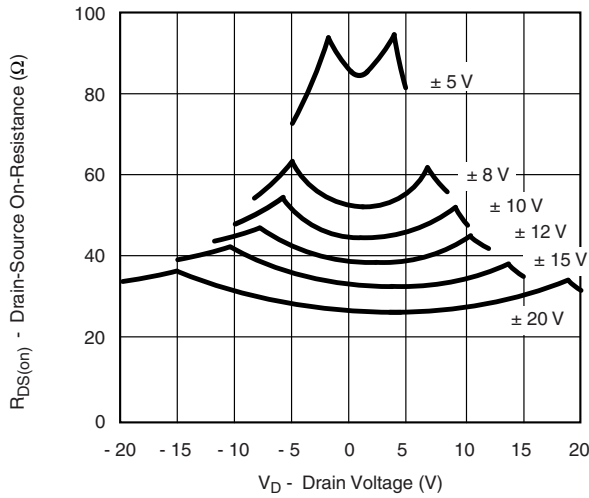
Notes

- a. Refer to PROCESS OPTION FLOWCHART
b. Room = 25 °C, full = as determined by the operating temperature suffix
c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
e. Guaranteed by design, not subject to production test
f. V_{IN} = input voltage to perform proper function

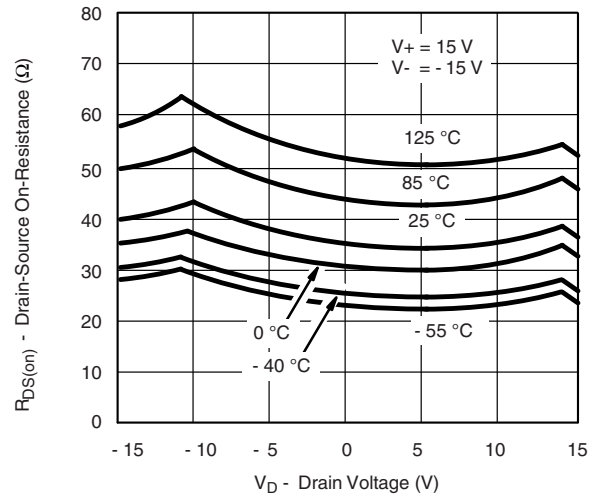
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



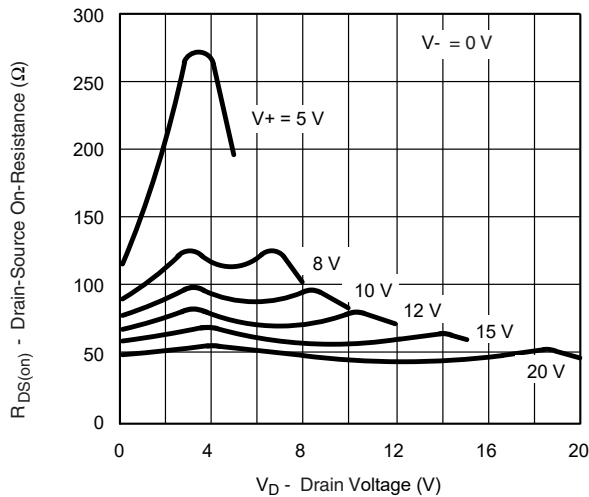
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



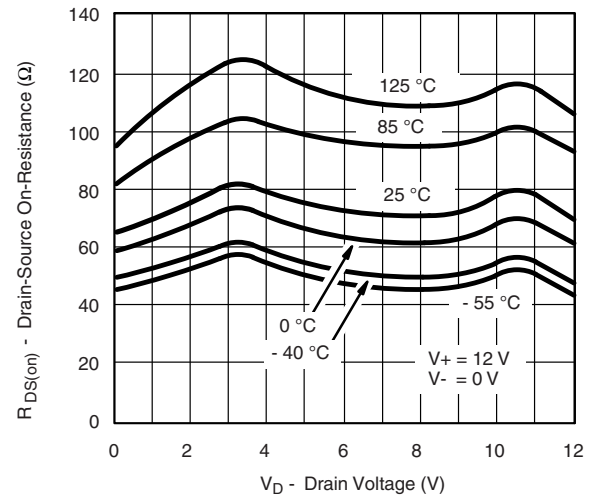
R_{DS(on)} vs. V_D and Power Supply Voltage



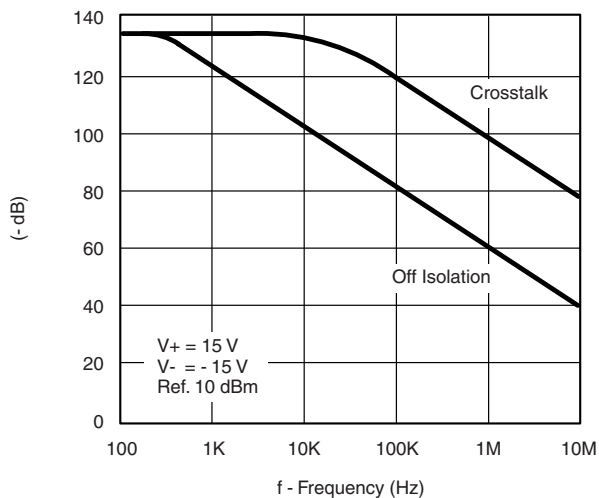
R_{DS(on)} vs. V_D and Temperature



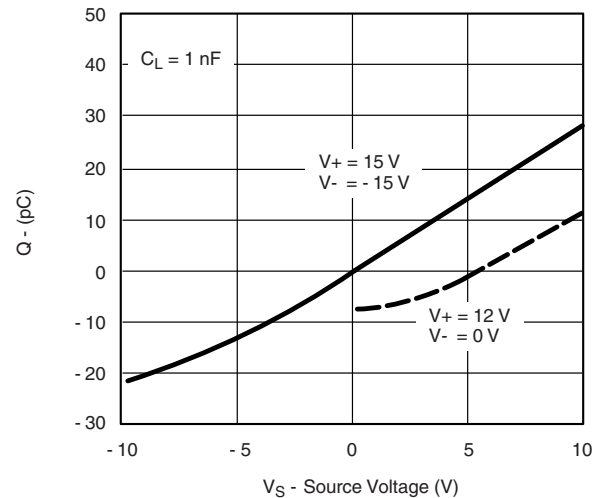
R_{DS(on)} vs. V_D and Unipolar Power Supply Voltage



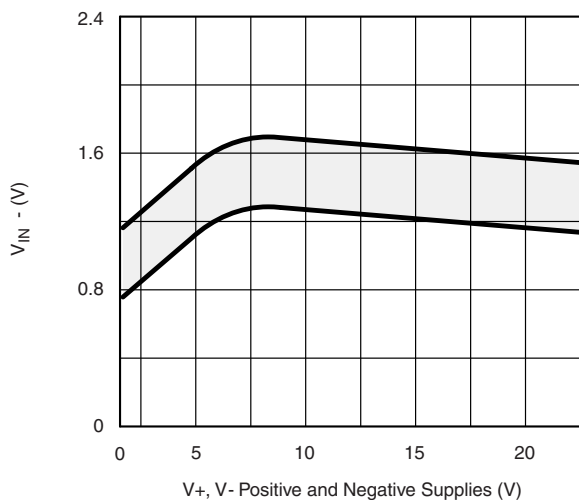
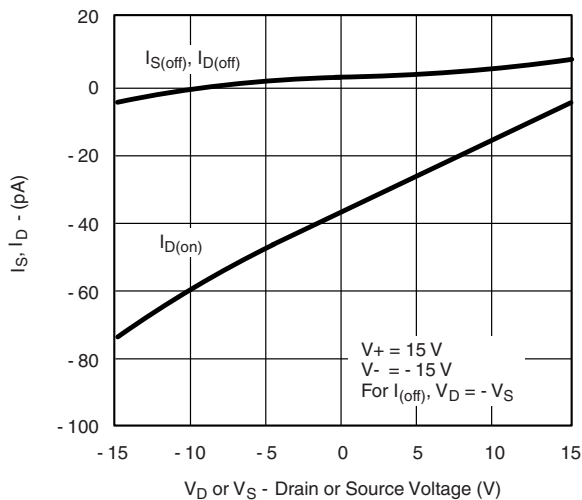
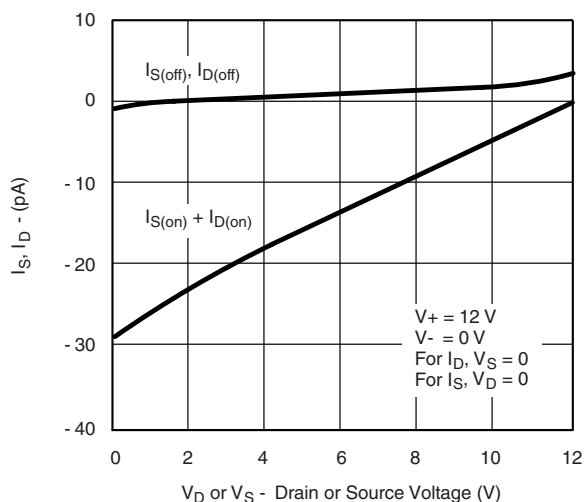
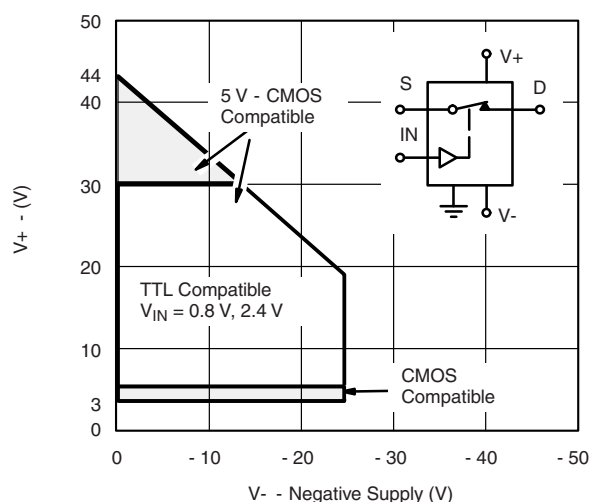
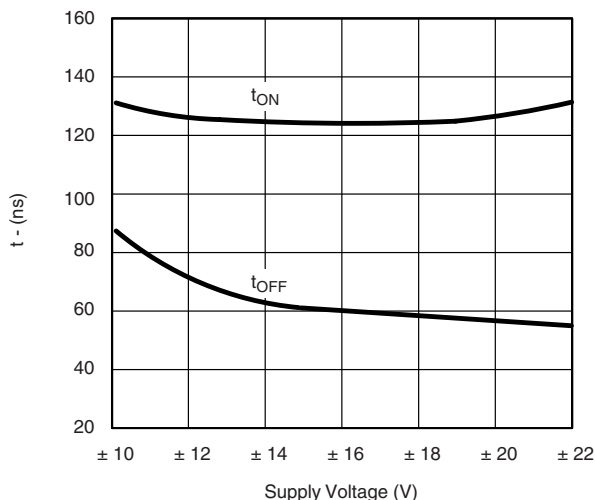
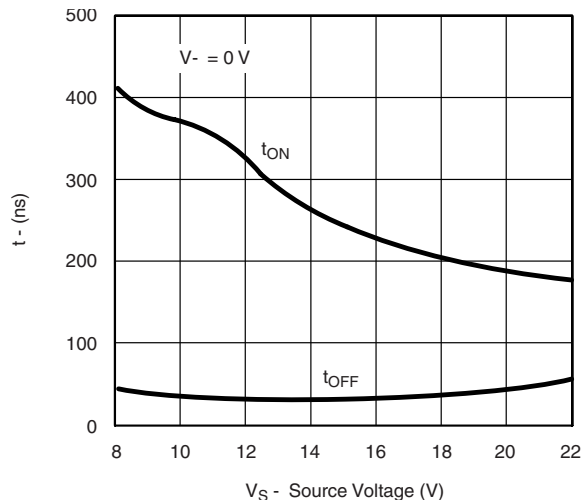
R_{DS(on)} vs. V_D and Temperature (Single 12-V Supply)

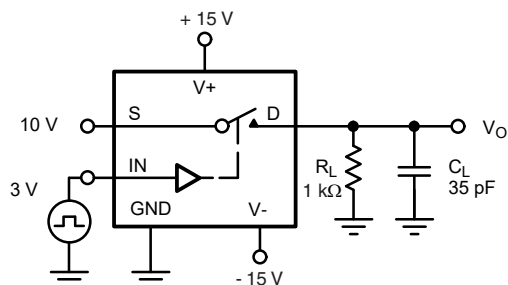
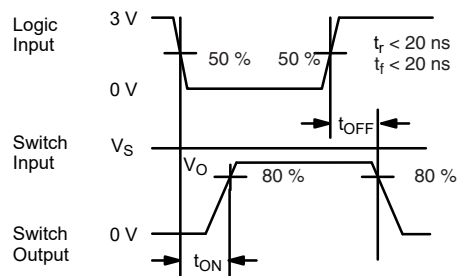


Crosstalk and Off Isolation vs. Frequency

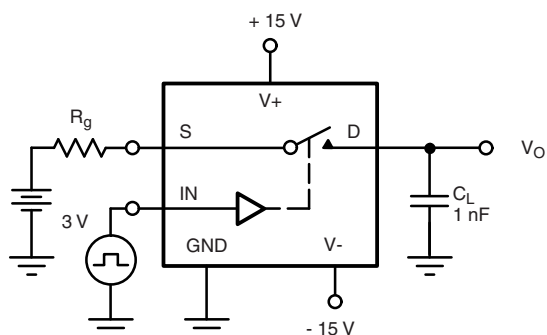
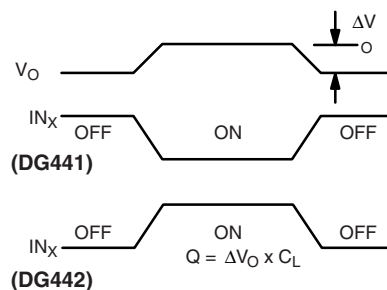
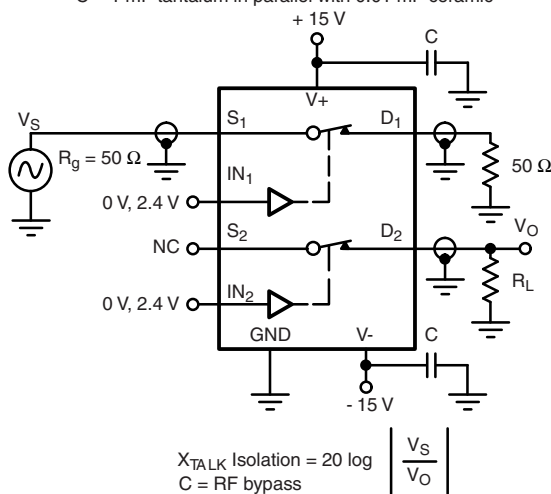


Charge Injection vs. Source Voltage

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Switching Threshold vs. Supply Voltage

Source/Drain Leakage Currents

Source/Drain Leakage Currents (Single 12 V Supply)

Operating Voltage

Switching Time vs. Power Supply Voltage

Switching Time vs. Power Supply Voltage

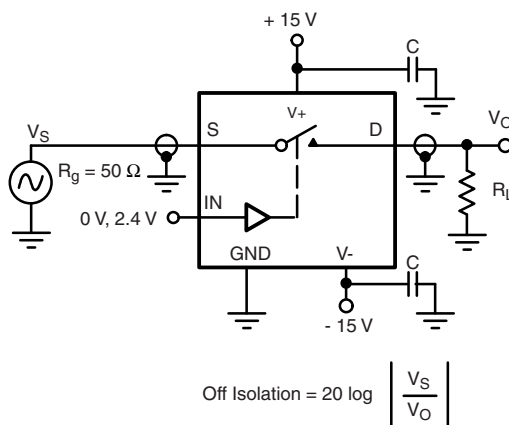
TEST CIRCUITS

 C_L (includes fixture and stray capacitance)


Note: Logic input waveform is inverted for DG442.

Fig. 2 - Switching Time

Fig. 3 - Charge Injection
 $C = 1 \text{ mF}$ tantalum in parallel with 0.01 mF ceramic


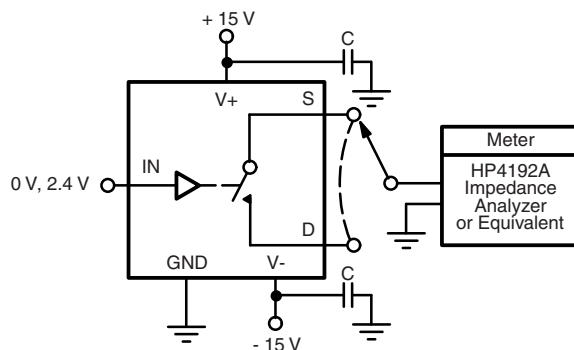
$$X_{\text{TALK}} \text{ Isolation} = 20 \log \left| \frac{V_S}{V_O} \right|$$

$$C = \text{RF bypass}$$

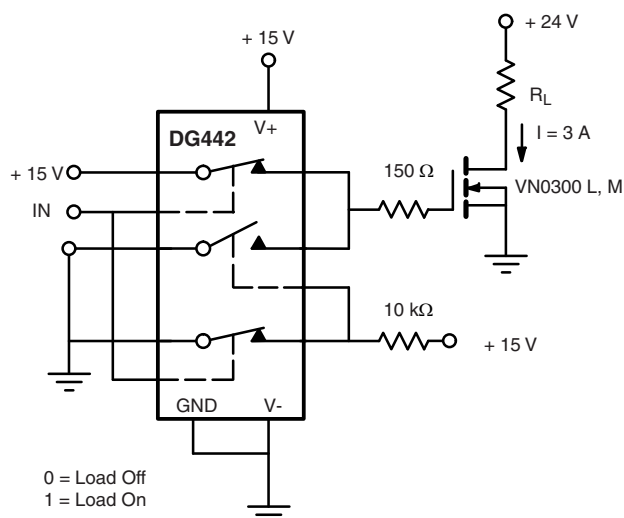
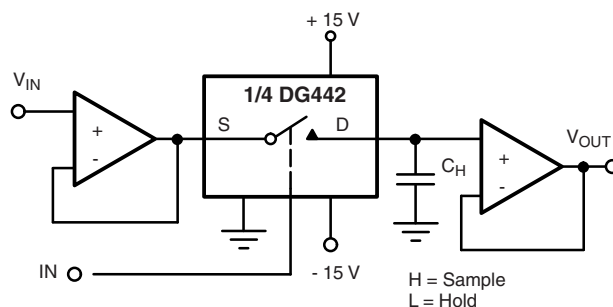
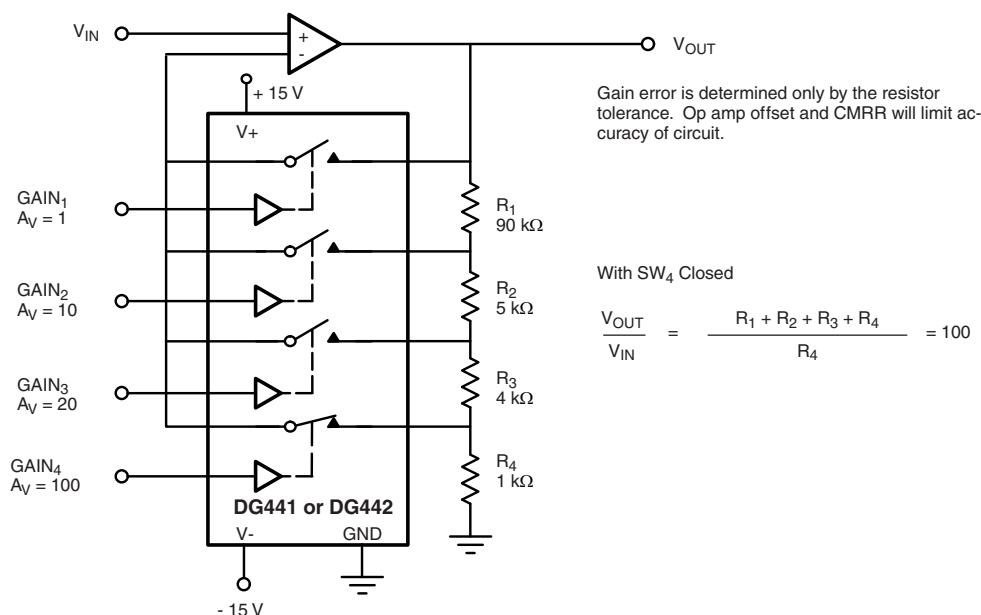
Fig. 4 - Crosstalk


$$\text{Off Isolation} = 20 \log \left| \frac{V_S}{V_O} \right|$$

Fig. 5 - Off Isolation


Fig. 6 - Source/Drain Capacitances

APPLICATIONS


Fig. 7 - Power MOSFET Driver

Fig. 8 - Open Loop Sample-and-Hold

Fig. 9 - Precision-Weighted Resistor Programmable-Gain Amplifier



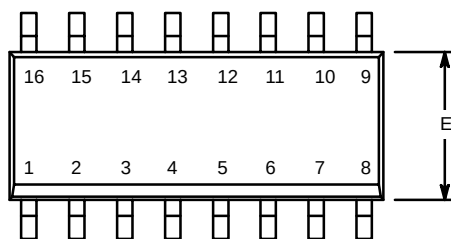
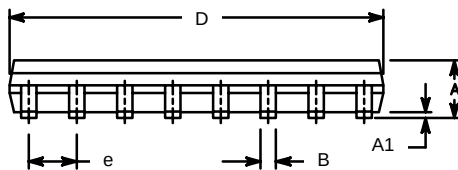
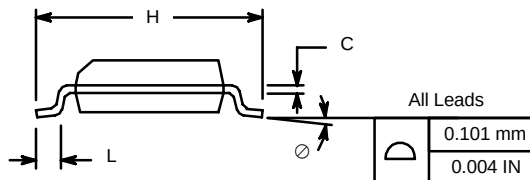
PRODUCT SUMMARY		
Part number	DG441	DG442
Status code	2	2
Configuration	SPST x 4, NC	SPST x 4, NO
Single supply min. (V)	5	5
Single supply max. (V)	36	36
Dual supply min. (V)	5	5
Dual supply max. (V)	22	22
On-resistance (Ω)	50	50
Charge injection (pC)	1	1
Source on capacitance (pF)	16	16
Source off capacitance (pF)	4	4
Leakage switch on typ. (nA)	0.08	0.08
Leakage switch off max. (nA)	0.5	0.5
-3 dB bandwidth (MHz)	-	-
Package	SO-16 (narrow) AS	SO-16 (narrow) AS
Functional circuit / applications	Multi purpose, instrumentation, medical and healthcare	Multi purpose, instrumentation, medical and healthcare
Interface	Parallel	Parallel
Single supply operation	Yes	Yes
Dual supply operation	Yes	Yes
Turn on time max. (ns)	250	250
Crosstalk and off isolation	-60	-60

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?61568.



SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012

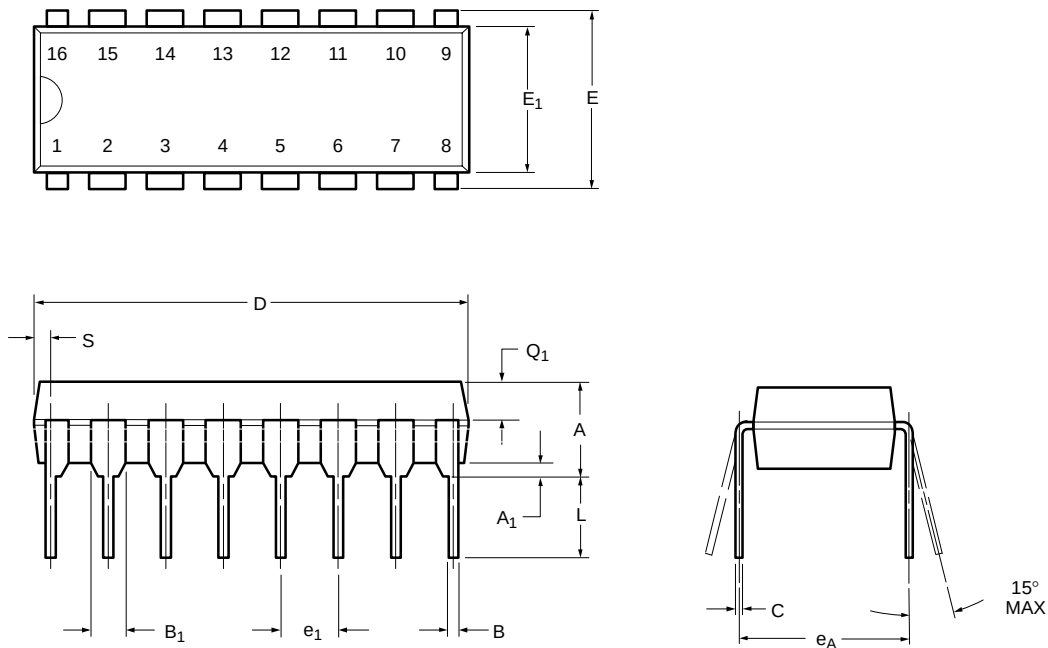


Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.38	0.51	0.015	0.020
C	0.18	0.23	0.007	0.009
D	9.80	10.00	0.385	0.393
E	3.80	4.00	0.149	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.50	0.93	0.020	0.037
Ø	0°	8°	0°	8°

ECN: S-03946—Rev. F, 09-Jul-01
DWG: 5300



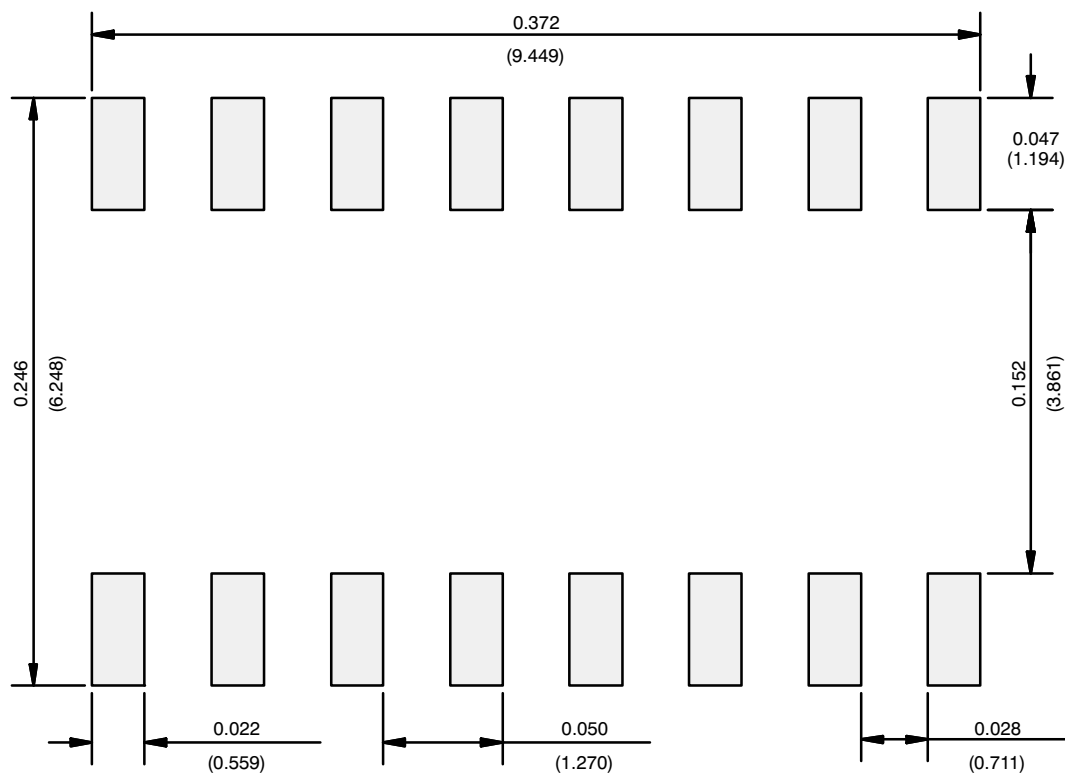
PDIP: 16-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	3.81	5.08	0.150	0.200
A ₁	0.38	1.27	0.015	0.050
B	0.38	0.51	0.015	0.020
B ₁	0.89	1.65	0.035	0.065
C	0.20	0.30	0.008	0.012
D	18.93	21.33	0.745	0.840
E	7.62	8.26	0.300	0.325
E ₁	5.59	7.11	0.220	0.280
e ₁	2.29	2.79	0.090	0.110
e _A	7.37	7.87	0.290	0.310
L	2.79	3.81	0.110	0.150
Q ₁	1.27	2.03	0.050	0.080
S	0.38	1.52	.015	0.060

ECN: S-03946—Rev. D, 09-Jul-01
DWG: 5482

RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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